

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) Field effect transistor comprising a source, a drain and a channel, respectively formed by source, drain and channel materials, the source, drain and channel materials being selected such that, for a NMOS type transistor, the electronic affinity ~~(Xd)~~ of the drain material is lower than the electronic affinity ~~(Xe)~~ of the channel material and such that, for a PMOS type transistor, the upper level ~~(Ed)~~ of the valence band of the drain material is higher the upper level ~~(Ee)~~ of the valence band of the channel material, transistor characterized in that, the transistor being of the normally on type, the electronic affinity ~~(Xs)~~ of the source material of NMOS transistor is higher than the electronic affinity ~~(Xe)~~ of the channel material of said NMOS transistor and the upper level ~~(Es)~~ of the valence band of the source material of a PMOS transistor is lower than the upper level ~~(Ee)~~ of the valence band of the channel material of said PMOS transistor.

2. (Currently Amended) Integrated circuit, ~~characterized in that it comprises~~ comprising PMOS type and NMOS type field effect transistors according to claim 1.